

SANYO	No.4321	2SK2012
		N-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

勝特力電材超市-龍山店 886-3-5773766
 勝特力電材超市-光復店 886-3-5729570
 勝特力電子(上海) 86-21-34970699
 勝特力電子(深圳) 86-755-83298787
<http://www.100y.com.tw>

Absolute Maximum Ratings at Ta = 25°C

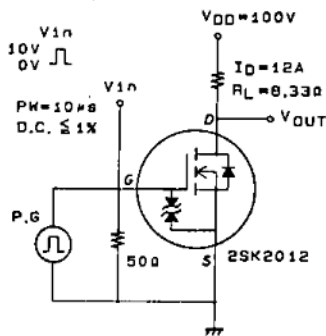
Drain-to-Source Voltage	V_{DS}	250	V	unit
Gate-to-Source Voltage	V_{GS}	±30	V	
Drain Current(DC)	I_D	18	A	
Drain Current(Pulse)	I_{DP}	72	A	
Allowable Power Dissipation	P_D	2.0	W	
		40	W	
Channel Temperature	T_{ch}	150	°C	
Storage Temperature	T_{stg}	-55 to +150	°C	

$T_c = 25^\circ C$

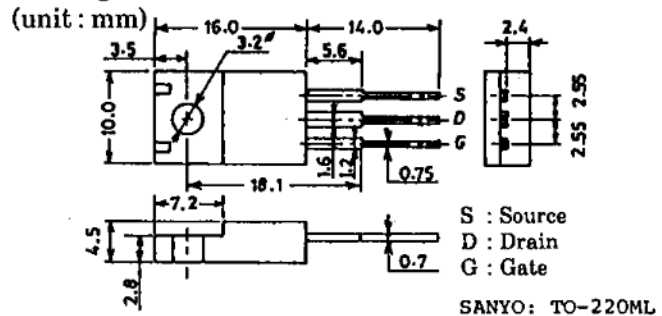
Electrical Characteristics at Ta = 25°C

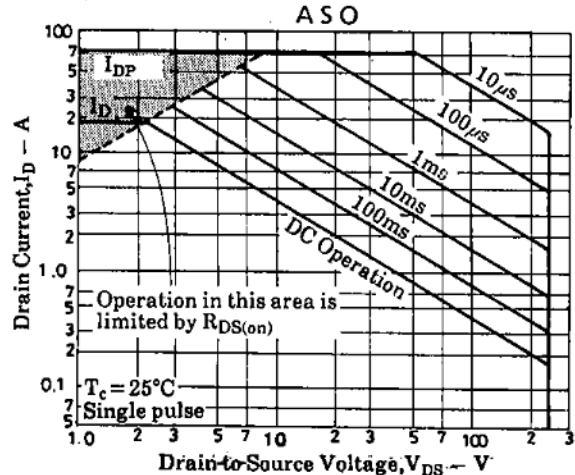
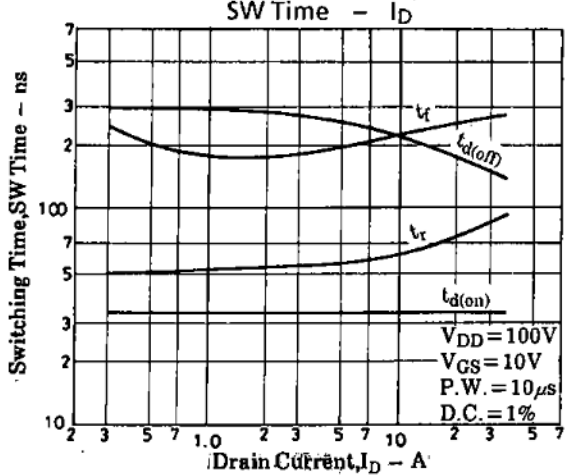
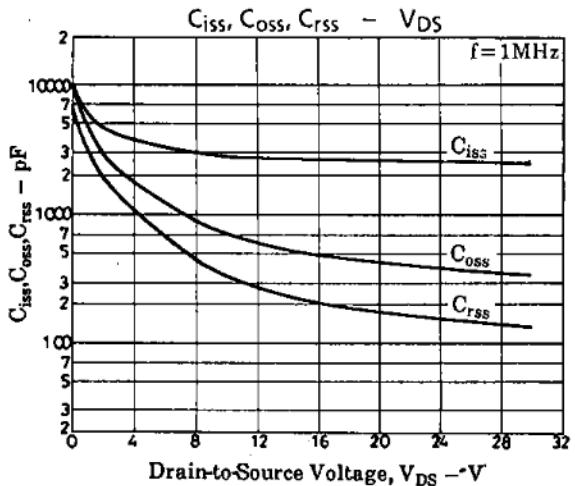
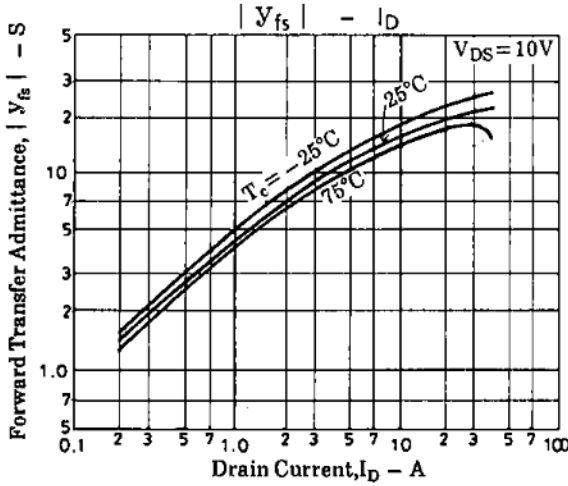
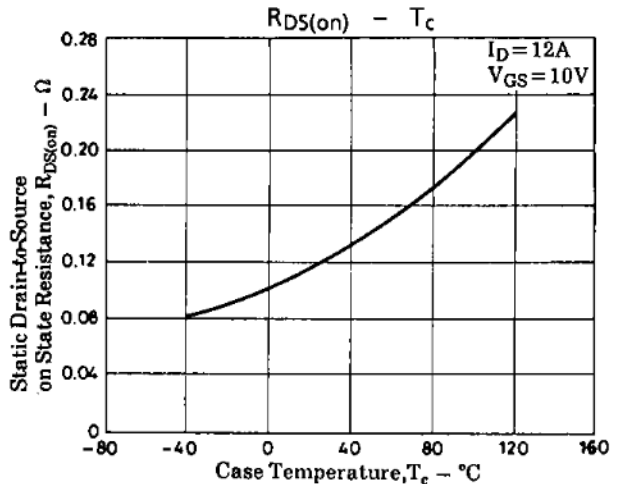
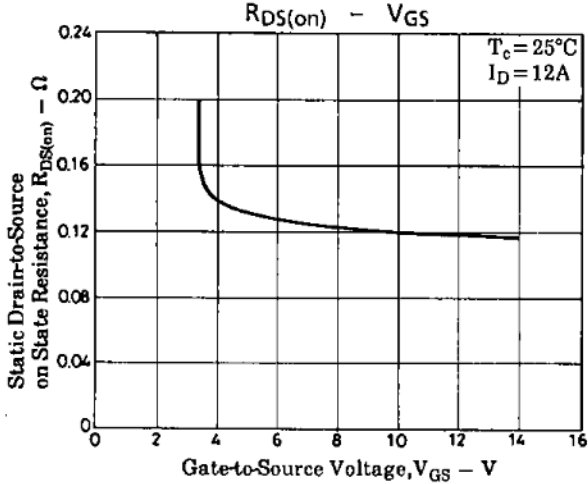
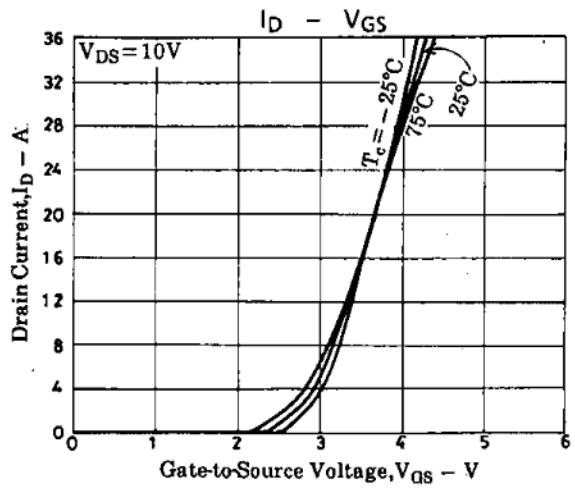
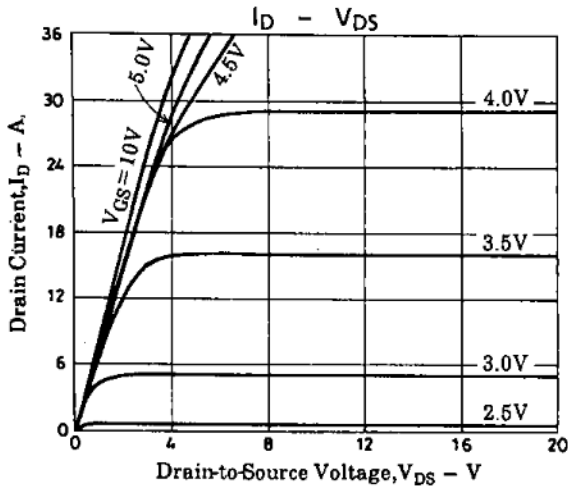
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1mA, V_{GS} = 0$	250			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	±30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 250V, V_{GS} = 0$			100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 25V, V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 1mA$	1.5		2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 12A$	11	18		S
Static Drain-to-Source on State Resistance	$R_{DS(on)}$	$I_D = 12A, V_{GS} = 10V$	0.12	0.16		Ω
Input Capacitance	C_{iss}	$V_{DS} = 20V, f = 1MHz$		2700		pF
Output Capacitance	C_{oss}	$V_{DS} = 20V, f = 1MHz$		450		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 20V, f = 1MHz$		180		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		35		ns
Rise Time	t_r	◇		65		ns
Turn-OFF Delay Time	$t_{d(off)}$	◇		210		ns
Fall Time	t_f	◇		235		ns
Diode Forward Voltage	V_{SD}	$I_S = 18A, V_{GS} = 0$	1.0	1.5		V

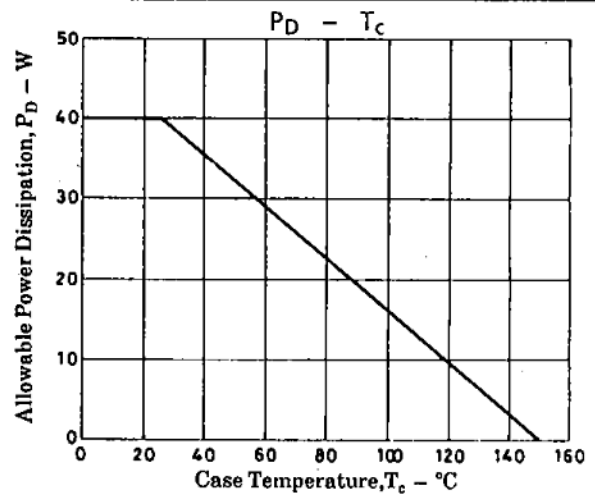
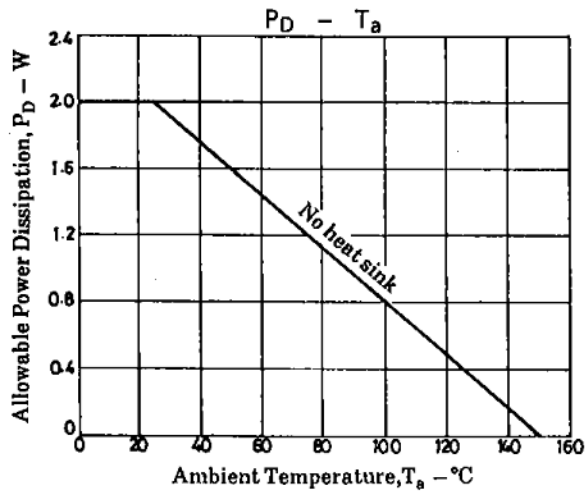
Switching Time Test Circuit



Package Dimensions 2063







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